

Nanoscale friction on 2D stacked MoS₂/graphene heterostructures

Zhao Liu¹⁾, Bartosz Szczefanowicz¹⁾, J. Marcelo J. Lopes²⁾, Antony George³⁾,
Roland Bennewitz^{1)*}

¹⁾INM – Leibniz Institute for New Materials, Campus D22, 66123 Saarbrücken, Germany.

²⁾Paul-Drude-Institut für Festkörperelektronik, Leibniz-Institut im Forschungsverbund Berlin e.V., Hausvogteiplatz 5-7, 10117 Berlin, Germany.

³⁾Friedrich Schiller University Jena, Institute of Physical Chemistry, 07743 Jena, Germany.

*Corresponding author: roland.bennewitz@leibniz-inm.de

Abstract: Stacked two-dimensional heterostructures attract much attention for their exotic electronic and mechanical properties. We investigated the structures and frictional properties of single layer MoS₂ on graphene/SiC(0001) by means of ultrahigh vacuum atomic force microscopy with non-contact and contact modes. Monolayer MoS₂ triangular islands with a size of ~200 nm are prepared by chemical vapor deposition on graphene/SiC(0001), which itself is prepared via SiC surface graphitization at high temperatures. Friction force microscopy at the atomic scale reveals a regime of low friction between the tip apex and the MoS₂ surface, with a friction coefficient ten times higher than that of the monolayer graphene/SiC(0001). MoS₂ islands are easily rotated or translated by the contacting AFM tip [1], while the second layer of graphene is usually stable under scanning. This finding indicates the weak interaction between MoS₂ and graphene. We measured a contact potential difference of ~300 mV between MoS₂ and graphene. This contrast opens the opportunity to tune the friction via bias on MoS₂/graphene heterostructures [2].

Keywords: 2D heterostructures, friction, MoS₂, graphene

- [1] Liao, M. Z. et al., “Twist angle-dependent conductivities across MoS₂/graphene heterojunctions”, *Nat. Commun.*, 9, 1, 2018, 1-6.
- [2] Peng, J. F. et al., “Friction behavior of monolayer molybdenum diselenide nanosheet under normal electric field”, *Phys. Lett. A*, 384, 7, 2020, 126166.